

# SPD04N60S5BTMA1

#### SPD04N60S5BTMA1 Information



For Reference Only

Part Number SPD04N60S5BTMA1
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 600V 4.5A TO252

Package TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## SPD04N60S5BTMA1 Specifications

Manufacturer Part Number         SPD04N60S5BTMA1           Manufacturer         Infineon Technologies           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-252-3, DPak (2 Leads + Tab), SC-63           Series         CoolMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         4.5A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5.5V @ 200µA           Gate Charge (Qg) (Max) @ Vgs         22.9nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         580pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         50W (Tc)           Rds On (Max) @ Id, Vgs         950 mOhm @ 2.8A, 10V           Operating Temperature         -55°C ~ 150°C (TI)           Mounting Type         Surface Mount           Supplier Device Package         PG-T0252-3           Package / Case         TO-252-3, DPak (2 Leads + Tab), SC-63           Report errors?		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-252-3, DPak (2 Leads + Tab), SC-63           Series         CoolMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         4.5A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5.5V @ 200μA           Gate Charge (Qg) (Max) @ Vgs         22.9nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         580pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         50W (Tc)           Rds On (Max) @ Id, Vgs         950 mOhm @ 2.8A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         PG-TO252-3           Package / Case         TO-252-3, DPak (2 Leads + Tab), SC-63	Manufacturer Part Number	SPD04N60S5BTMA1
Package         TO-252-3, DPak (2 Leads + Tab), SC-63           Series         CoolMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         4.5A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5.5V @ 200μA           Gate Charge (Qg) (Max) @ Vgs         22.9nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         580pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         50W (Tc)           Rds On (Max) @ Id, Vgs         950 mOhm @ 2.8A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         PG-TO252-3           Package / Case         TO-252-3, DPak (2 Leads + Tab), SC-63	Manufacturer	Infineon Technologies
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Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  5.5V @ 200μA  Gate Charge (Qg) (Max) @ Vgs  1nput Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ±20V  FET Feature  Power Dissipation (Max)  SoW (Tc)  Rds On (Max) @ Id, Vgs  950 mOhm @ 2.8A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  PG-TO252-3  Package / Case  TO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	600V
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	Supplier Device Package	PG-TO252-3
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

#### SPD04N60S5BTMA1 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

#### SPD04N60S5BTMA1 Payment Methods



















### SPD04N60S5BTMA1 Shipping Methods













If you have any question about SPD04N60S5BTMA1, please do not hesitate to contact us!

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